



industrial

GOODRAM Industrial

DDR3 SODIMM ECC 204pin

extended temperature

DATASHEET

Document number:
Version: 1.0
Date: November 2020

Wilk Elektronik S.A.
Mikołowska 42
43-173 Łaziska Górne, Poland
Tel.: +48 32 736 90 00, Fax.: +48 32 736 90 01
E-mail: sales@goodram.com

All rights are strictly reserved. Any portion of this paper shall not be reproduced, copied or translated to any other forms without permission from Wilk Elektronik S.A.

This document is subject to change without any notice.

Please contact your Wilk Elektronik S.A. sales representative for details as to environmental matters such as the RoHS compatibility of Product. Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Wilk Elektronik S.A. assumes no liability for damages or losses occurring as a result of noncompliance with applicable laws and regulations.



industrial

Unbuffered DDR3 SODIMM ECC datasheet

REVISION HISTORY

| VERSION | CHANGES | DATE |
|---------|-----------------|------------|
| 1.0 | Initial release | 02.11.2020 |



industrial

TABLE OF CONTENTS

REVISION HISTORY 2

PRODUCT OVERVIEW 4

PRODUCT DETAILS 5

PART NUMBERS AND TIMING PARAMETERS 6

ADDRESSING 6

PHYSICAL DIMENSION 7

STANDARDS & REFERENCES 8

SAFETY PRECAUTIONS 8

NOTES ON USAGE 9

PRODUCT OVERVIEW

| | |
|------------------------------------|---|
| Module Form Factor | 204-pin, unbuffered small-outline dual in-line memory module (SODIMM) |
| Interface | DDR3, JEDEC compliant JESD79-3 |
| Capacity | 4GB – 8GB |
| Fast Data Transfer Rates | PC3-12800 @1600 MT/s |
| DRAM IC Type | 256Mx8, 512Mx8 |
| Power Supply | VDD = 1.50V, VDDSPD = 3.0V - 3.6V |
| ECC Support | YES |
| Registered | NO |
| Thermal sensor | YES |
| Temperature range ^{Note1} | Operating: -40°C ~ +85°C; Storage: -40°C ~ +100°C |
| Fly-by topology | YES |
| Gold edge contacts | YES |
| RoHS compliant | YES |

Notes:

1. According to IEC-60068-2-1/2/14 standards

PRODUCT DETAILS

General Description

DDR3 SDRAM modules are high-speed, CMOS dynamic random access memory modules that use internally configured 8-bank DDR3 SDRAM devices. DDR3 SDRAM modules use DDR architecture to achieve high-speed operation. DDR3 architecture is essentially an 8n-prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write access for the DDR3 SDRAM module effectively consists of a single bit 8n-bit-side, one-clock-cycle data transfer at the internal DRAM core and eight corresponding n-bit-wide, one-half-clock-cycle data transfers at the I/O pins.

Fly-By Topology

DDR3 modules use faster clock speeds than earlier DDR technologies, making signal quality more important than ever. For improved signal quality, the clock, control, command and address buses have been routed in a fly-by topology, where each clock, control, command and address pin on each DRAM is connected to a single trace and terminated (rather than a tree structure, where the termination is off the module near the connector). Inherent to fly-by topology, the timing skew between the clock and DQS signals can be easily accounted for by using the write-leveling feature of DDR3.

Thermal Sensor Operations

The temperature from the integrated thermal sensor is monitored and converts into a digital word via the I²C bus. System designers can use the user-programmable registers to create a custom temperature-sensing solution based on system requirements. Programming and configuration details comply with JEDEC standard 21-C page 4.7-1 "Definition of the TSE2002av. Serial Presence Detect with Temperature Sensor".

PART NUMBERS AND TIMING PARAMETERS

| PART NUMBER | MODULE DENSITY | CONFIGURATION | MODULE BANDWIDTH | MEMORY CLOCK / DATA RATE | CLOCK CYCLES (CL- ^T RCD- ^T RP) |
|--------------|----------------|---------------|------------------|--------------------------|--|
| GR3A4G160D8I | 4GB | 256Mx8 DR | 12.8 GB/s | 1.25ns/1600 MT/s | 11-11-11 |
| GR3A8G160D8I | 8GB | 512Mx8 DR | 12.8 GB/s | 1.25ns/1600 MT/s | 11-11-11 |

DR – Double Rank

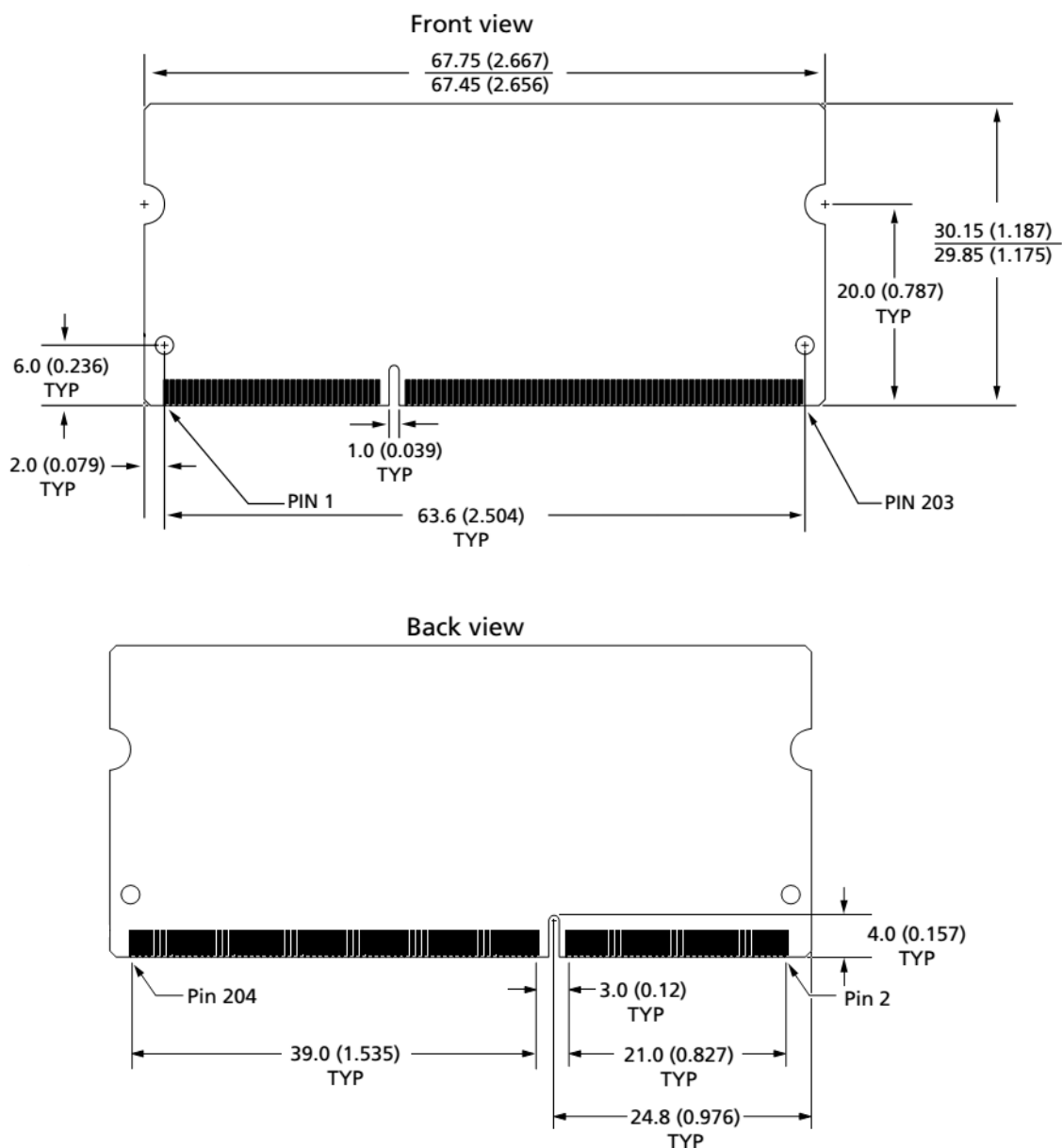
I – extended temperature

ADDRESSING

| PARAMETER | 4GB DR | 8GB DR |
|----------------------|-----------------|-----------------|
| Refresh count | 8K | 8K |
| Row address | 32K A[14:0] | 64K A[15:0] |
| Device bank address | 8 BA[2:0] | 8 BA[2:0] |
| Device configuration | 4Gb (256Mx8) | 8Gb (512Mx8) |
| Column address | 1K A[9:0] | 1K A[9:0] |
| Module rank address | 2S#[1:0] | 2S#[1:0] |

PHYSICAL DIMENSION

Dimensions: 67.6mm (L) * 30mm (W)



Note:

1. All dimensions are in millimeters (inches). MAX/MIN or typical (TYP) where noted.
2. The dimensional diagram is for reference only. Refer to JEDEC document for additional design dimensions.



industrial

STANDARDS & REFERENCES

The following table is to list out the standards that have been adopted for designing the product.

| STANDARD USED | ACRONYM/SOURCE |
|---------------|--|
| RoHS | Restriction of Hazardous Substances Directive |
| CE | Consumer electronics certification; please contact us for further information. |

SAFETY PRECAUTIONS

Do not bend, crush, drop or place heavy objects on top of the Product. Do not use tweezers, pliers or similar items that could damage the Product. Take particular care when inserting or removing the Product. Stop using the Product when the Product does not work properly. Failure to follow these instructions could result in fire, damage to the Product and/or other property, and/or personal injury including burns and electric shock.

Keep out of reach of small children. Accidental swallowing may cause suffocation or injury. Contact a doctor immediately if you suspect a child has swallowed the Product.

Do not directly touch the interface pins, put them in contact with metal, strike them with hard objects or cause them to short. Do not expose to static electricity.

Do not disassemble or modify the Product. This may cause electric shock, damage to the Product or fire.

NOTES ON USAGE

The Product contains nonvolatile semiconductor memory. Do not use the Product in accordance with a method of usage other than that written in the manual. This may cause the destruction or loss of data.

To protect against accidental data loss, you should back up your data frequently on more than one type of storage media. Wilk Elektronik S.A. assumes no liability for destruction or loss of data recorded on the Card for any reason.

When used over a long period of time or repeatedly, the reading, writing and deleting capabilities of the Product will eventually fail, and the performance speed of the Product may decrease below the original speed specific to the Product's applicable class.

If the Product is to be transferred or destroyed, note that the data it contained may still be recoverable unless it is permanently deleted by third-party deletion software or similar means beforehand.

Product is intended for use in general electronics applications and selected industrial applications and any other specific applications as expressly stated in this document. Product is neither intended nor warranted for use in equipment or systems where failure may cause loss of human life, bodily injury, serious property damage or serious public impact ("Unintended Use"). Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment or equipment used to control combustions or explosions. Do not use Product for Unintended Use unless specifically permitted in this document.

No parts of this document may be reproduced, stored in a retrieval system or transmitted in any form or by any means, mechanical, electric, photocopying, recording or otherwise, without permission of Wilk Elektronik S.A.

Wilk Elektronik S.A does not make any warranty, express or implied, with respect to this document, including as to licensing, Non-infringement, merchantability or fitness for a particular purpose.